

Quick Start Micro Training LLC
Very Quick Start™ Microelectronics Course
 Dr. Ted Dellin

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**7-Hour Narrated E Learning Course
 (Also Webinar or In-Person Class)**

**SAMPLE SLIDES
 FROM COURSE**

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Outline of Class

Introduction
 (1. Introduction, 2. Background Review)

Special Properties of Semiconductors
 (3. Semis are Special 4. Electrons & holes, 5. n & p type
 6. Currents, 7. pn Junctions, 8. External voltage on pn Junction)

MOS Transistor & CMOS IC
 (9. MOS capacitor, 10. MOS transistor, 11. ICs & scaling)

Making an IC
 (12. Overview, 13. Design & Test, 14. Unit Processes
 15. Front End Process, 16. Back End Process, 17. Packaging)

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**Engineering Semiconductor Properties
 Leads to Useful Devices**

Semiconductors Have Electronic Special Properties

We Can Engineer (Control) Those Properties
 During Design & Manufacturing By Applying Voltages During Device Operation

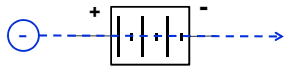
2 Basic Building Blocks of Electronic & Optoelectronics
 Junctions (Semi/Semi, Semi/Metal) MOS Capacitor

Very Useful Devices
 Rectifiers, Transistors, ICs, Photodetectors, Solar Cells, LEDs, Lasers

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**A Voltage Source (e.g., Battery)
 Supplies Energy**

Battery of Voltage, V

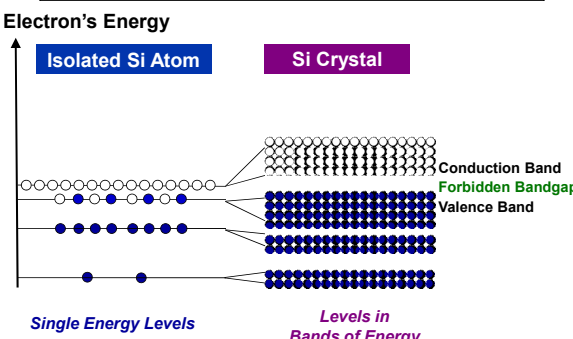


- Charges gain energy going through a battery
- Electrons gain energy from + to – side of battery
- Energy Gained = Amount of Charge x Voltage
- An electron going through a 1V battery gains 1 eV (electron Volt, 1.6E-19 Joules)

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**Single Energy Levels of Atoms Become
 Bands (Ranges of Energy) in Crystals**

Electron's Energy



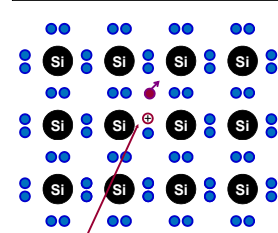
Isolated Si Atom Si Crystal

Conduction Band
 Forbidden Bandgap
 Valence Band

Single Energy Levels Levels in Bands of Energy

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The Positively Charged "Hole"



- The site of the missing valence electron is called a "hole"
- There is a charge of +1 at the hole
 - 14 + protons surrounded by only 13 – electrons
- The hole can move through the crystal
 - An electron from an adjacent atom can fill an existing hole and in the process create a new hole at the adjacent atom

"Hole" (Missing Valence Electron)

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Replacing a Silicon Atom With Phosphorus Makes Silicon n Type (Excess Electrons)

n Type (Excess Electron) Si
P substitutionally replaces *Si* in the lattice. *P*'s 5th valence electron is free to move about crystal.

● Si Valence Electron
 ● P Valence Electron

Extra Phosphorous (P) Electron

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A "Junction" Is Formed Whenever Two Different Semiconductors Are Joined

- "Bulk" regions of the semiconductors remained essentially unchanged
- Inside the junction many interesting effects can occur
 - E.g., built-in voltage and electric field and diffusion barriers

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Current Through Junction Vs. Externally Applied Voltage ("IV Curve")

Reverse bias (p semi to - voltage) Zero Bias Forward bias (p semi to + voltage)

0V - No Current (Diffusion & Drift Currents Cancel)

"Breakdown" Very Small Reverse "Leakage" Current Due to Generation & Drift (No Diffusion) Very Large Forward Current As Applied Voltage Reduces Diffusion Barrier

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$V_{GATE} \geq V_{THRESHOLD}$ Inversion: Conductive Channel Formed

Gate: $V_{GATE} \geq V_{THRESHOLD}$ Positive Charges on Gate

Oxide

Maximum Depletion Region

Bulk p Type Silicon

0 Volts

Inversion Layer of Mobile Electrons
 Surface inverted from p to n type

Depletion region reaches its maximum depth at threshold
 Above threshold have strong surface inversion layer of negative electrons

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"Only Two Things" Division of Labor in MOS Transistor

1. Gate: Mobile Charges
2. Drain: Average Motion of Those Charges In One Direction

- A Gate Voltage, $V_G > V_{THRESHOLD}$ creates a surface layer of mobile charges ("inversion")
- Drain Voltage produces an electric field which moves electrons from source to drain

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Transistors + Electrical Interconnection = Integrated Circuit (IC)

- IC contains:
 - Lots of transistors
 - Electrical wiring between transistors and the outside world
- The layout of the transistors plus interconnection determine the function of the IC
 - Digital IC
 - Analog IC
 - Memory

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